



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shuichi Kikuchi et al.
Serial No. : 09/943,667
Filed : August 31, 2001
Title : SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Art Unit : 2822
Examiner : Thomas, Toniae M.

Commissioner for Patents
Washington, D.C. 20231

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RESPONSE

In response to the action mailed September 13, 2002, please amend the application as follows:

In the specification:

A substitute specification is provided herein. No new matter has been added in the substitute specification.

In the claims:

Please cancel claims 4 to 7 without prejudice.

Please amend claims 1 to 3 as follows:

- a
- 1. (Amended) A semiconductor device comprising:
a gate electrode formed on a first conductive type semiconductor substrate through a gate oxide film;
a first low concentration drain region of a second conductive type, provided at one end of said gate electrode;

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

January 13, 2003

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